DMN3110S-7 Datasheet

https://www.DiGi-Electronics.com

DiGi Electronics Part Number	DMN3110S-7-DG
Manufacturer	Diodes Incorporated
Manufacturer Product Number	DMN3110S-7
Description	MOSFET N-CH 30V 2.5A SOT-23
Detailed Description	N-Channel 30 V 2.5A (Ta) 740mW (Ta) Surface Mount SOT-23-3

Tel: +00 852-30501935

RFQ Email: Info@DiGi-Electronics.com

Purchase and inquiry

Manufacturer Product Number:	Manufacturer:
DMN3110S-7	Diodes Incorporated
Series:	Product Status:
-	Active
FET Type:	Technology:
N-Channel	MOSFET (Metal Oxide)
Drain to Source Voltage (Vdss):	Current - Continuous Drain (Id) @ 25°C:
30 V	2.5A (Ta)
Drive Voltage (Max Rds On, Min Rds On):	Rds On (Max) @ Id, Vgs:
4.5V, 10V	73mOhm @ 3.1mA, 10V
Vgs(th) (Max) @ Id:	Gate Charge (Qg) (Max) @ Vgs:
3V @ 250µA	8.6 nC @ 10 V
Vgs (Max):	Input Capacitance (Ciss) (Max) @ Vds:
±20V	305.8 pF @ 15 V
FET Feature:	Power Dissipation (Max):
-	740mW (Ta)
Operating Temperature:	Mounting Type:
-55°C ~ 150°C (TJ)	Surface Mount
Supplier Device Package:	Package / Case:
SOT-23-3	TO-236-3, SC-59, SOT-23-3
Base Product Number:	
DMN3110	

Environmental & Export classification

RoHS Status:	Moisture Sensitivity Level (MSL):
ROHS3 Compliant	1 (Unlimited)
REACH Status:	ECCN:
REACH Unaffected	EAR99
HTSUS:	
8541.21.0095	

Lead-free Green

DMN3110S

N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

$V_{(BR)DSS}$	$R_{DS(ON)}$ max	I_D max T_A = +25°C
30V	73mΩ @ V_{GS} = 10V	3.3A
	110mΩ @ V_{GS} = 4.5V	2.7A

Features and Benefits

- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **For automotive applications requiring specific change control (i.e.: parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please refer to the related automotive grade (Q-suffix) part. A listing can be found at https://www.diodes.com/products/automotive/automotive-products/.**
- **This part is qualified to JEDEC standards (as references in AEC-Q) for High Reliability. https://www.diodes.com/quality/product-definitions/**

Description and Applications

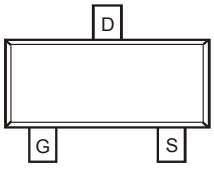
This MOSFET has been designed to minimize the on-state resistance ($R_{DS(on)}$) and yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

- General Purpose Interfacing Switch
- Power Management Functions
- Boost Application
- Analog Switch

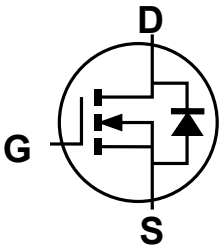
Mechanical Data

- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See diagram
- Terminals: Finish—Matte Tin Annealed Over Copper Lead-Frame. Solderable per MIL-STD-202, Method 208 e3
- Weight: 0.027 grams (approximate)

Top View



Pin Configuration



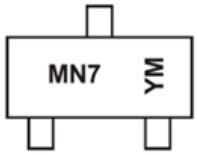
Internal Schematic

Ordering Information (Note 4)

Part Number	Case	Packaging
DMN3110S-7	SOT23	3000/Tape & Reel

Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



MN7 = Product Type Marking Code
YM = Date Code Marking
Y or $\overline{Y}$ = Year (ex: I = 2021)
M = Month (ex: 9 = September)

Date Code Key

Year	2021	2022	2023	2024	2025	2026	2027	2028	2029	2030	2031	2032
Code	I	J	K	L	M	N	O	P	R	S	T	U

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

Maximum Ratings (@ T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Units
Drain-Source Voltage			V_{DSS}	30	V
Gate-Source Voltage			V_{GSS}	±20	V
Continuous Drain Current (Note 5) V_{GS} = 10V	Steady State	T_A = +25°C T_A = +70°C	I_D	2.5 2.0	A
Continuous Drain Current (Note 6) V_{GS} = 10V	Steady State	T_A = +25°C T_A = +70°C	I_D	3.3 2.7	A
Continuous Drain Current (Note 6) V_{GS} = 10V	t≦10sec	T_A = +25°C T_A = +70°C	I_D	3.8 3.1	A
Continuous Drain Current (Note 6) V_{GS} = 4.5V	Steady State	T_A = +25°C T_A = +70°C	I_D	2.7 2.1	A
Pulsed Drain Current (Note 7)			I_{DM}	25	A

Thermal Characteristics (@ T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Units
Total Power Dissipation (Note 5)	P_D	0.74	W
Thermal Resistance, Junction to Ambient (Note 5)	$R_{\theta JA}$	173.4	°C/W
Total Power Dissipation (Note 6)	P_D	1.3	W
Thermal Resistance, Junction to Ambient (Note 6)	$R_{\theta JA}$	99.1	°C/W
Total Power Dissipation (Note 6) t≦10sec	P_D	1.8	W
Thermal Resistance, Junction to Ambient (Note 6) t≦10sec	$R_{\theta JA}$	72	°C/W
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to +150	°C

Notes: 5. Device mounted on FR-4 PCB, with minimum recommended pad layout.
6. Device mounted on FR-4 substrate PC board, 2oz copper, on 1inch square copper plate
7. Device mounted on minimum recommended pad layout test board, 10μs pulse duty cycle = 1%

Electrical Characteristics (@ T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)						
Drain-Source Breakdown Voltage	BV_{DSS}	30	-	-	V	V_{GS} = 0V, I_D = 250μA
Zero Gate Voltage Drain Current @T_C = +25°C	I_{DSS}	-	-	1.0	μA	V_{DS} = 30V, V_{GS} = 0V
Gate-Source Leakage	I_{GSS}	-	-	±100	nA	V_{GS} = ±20V, V_{DS} = 0V
ON CHARACTERISTICS (Note 8)						
Gate Threshold Voltage	$V_{GS(th)}$	1.0	-	3.0	V	V_{DS} = V_{GS}, I_D = 250μA
Static Drain-Source On-Resistance	$R_{DS\ (ON)}$	-	54	73	mΩ	V_{GS} = 10V, I_D = 3.1A
		-	88	110		V_{GS} = 4.5V, I_D = 2A
Forward Transfer Admittance	$\|Y_{fs}\|$	-	4.8	-	mS	V_{DS} = 10V, I_D = 3.1A
Diode Forward Voltage (Note 6)	V_{SD}	-	0.75	1.0	V	V_{GS} = 0V, I_S = 1A
DYNAMIC CHARACTERISTICS (Note 9)						
Input Capacitance	C_{iss}	-	305.8	-	pF	V_{DS} = 15V, V_{GS} = 0V, f = 1.0MHz
Output Capacitance	C_{oss}	-	39.9	-	pF	
Reverse Transfer Capacitance	C_{rss}	-	39.5	-	pF	
Gate Resistance	R_g	-	1.4	-	Ω	V_{DS} = 0V, V_{GS} = 0V,f = 1.0MHz
Total Gate Charge (V_{GS} = 4.5V)	Q_g	-	4.1	-	nC	V_{GS} = 10V, V_{DS} = 10V, I_D = 3A
Total Gate Charge (V_{GS} = 10V)	Q_g	-	8.6	-	nC	
Gate-Source Charge	Q_{gs}	-	1.2	-	nC	
Gate-Drain Charge	Q_{gd}	-	1.5	-	nC	
Turn-On Delay Time	$t_{D(on)}$	-	2.6	-	ns	V_{DD} = 15V, V_{GS} = 10V, R_L = 47Ω, R_G = 3Ω,
Turn-On Rise Time	t_r	-	4.6	-	ns	
Turn-Off Delay Time	$t_{D(off)}$	-	13.1	-	ns	
Turn-Off Fall Time	t_f	-	2.5	-	ns	

Notes: 8. Short duration pulse test used to minimize self-heating effect.
9. Guaranteed by design. Not subject to product testing.

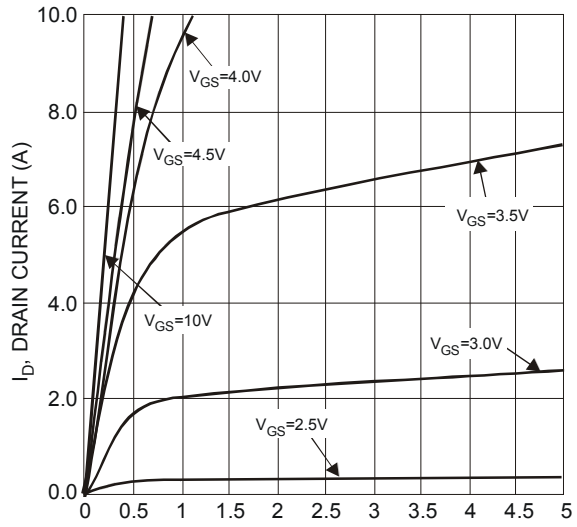


Fig. 1 Typical Output Characteristics

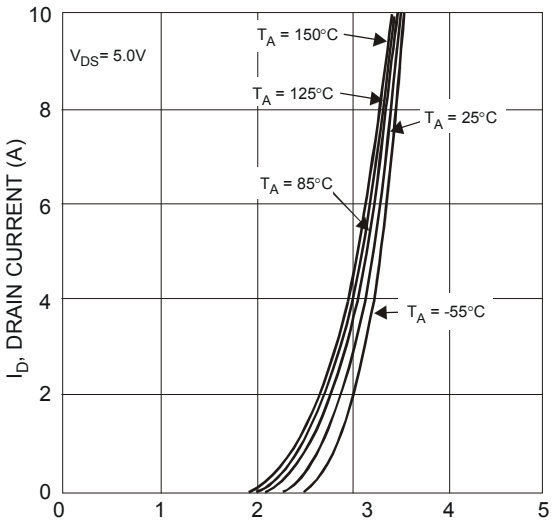


Fig. 2 Typical Transfer Characteristics

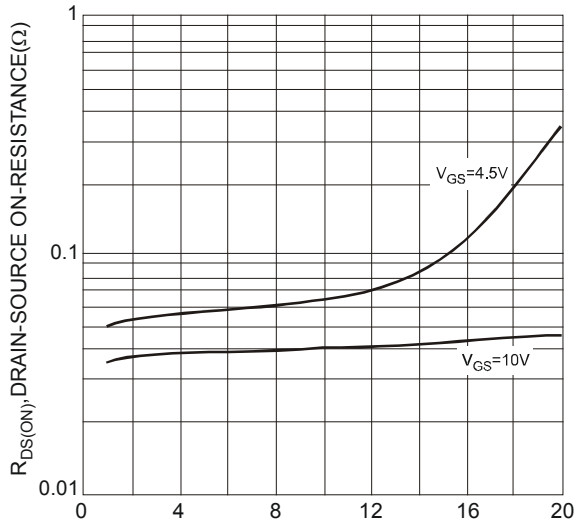


Fig. 3 Typical On-Resistance vs. Drain Current and Gate Voltage

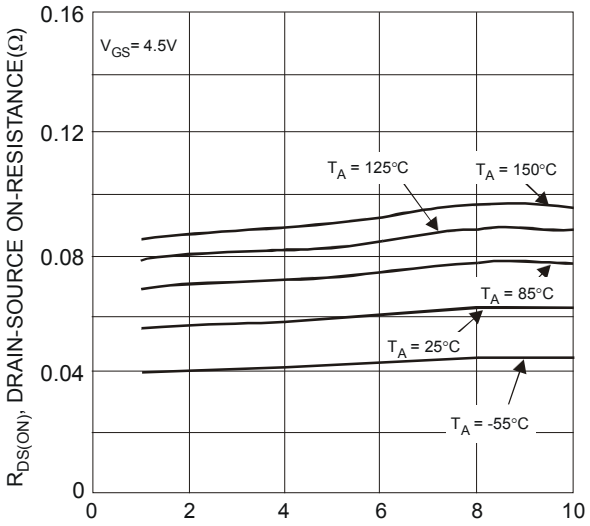


Fig. 4 Typical On-Resistance vs. Drain Current and Temperature

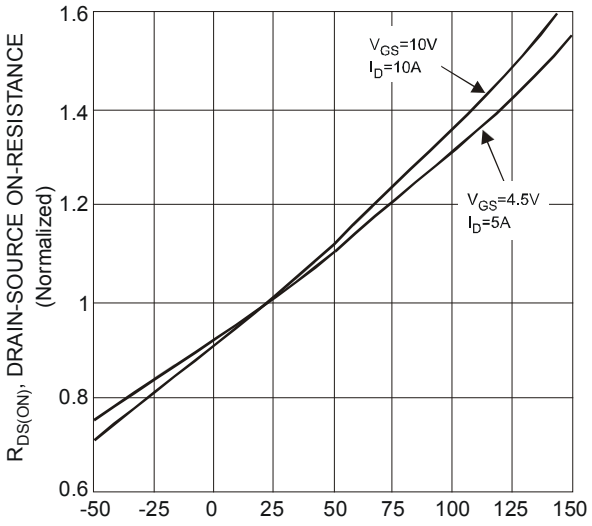


Fig. 5 On-Resistance Variation with Temperature

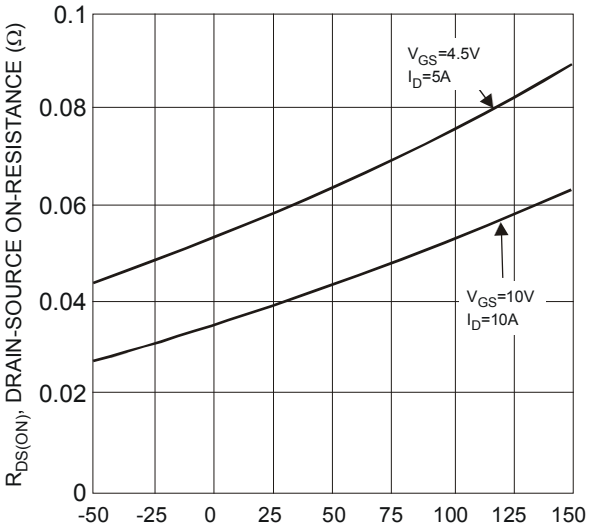


Fig. 6 On-Resistance Variation with Temperature

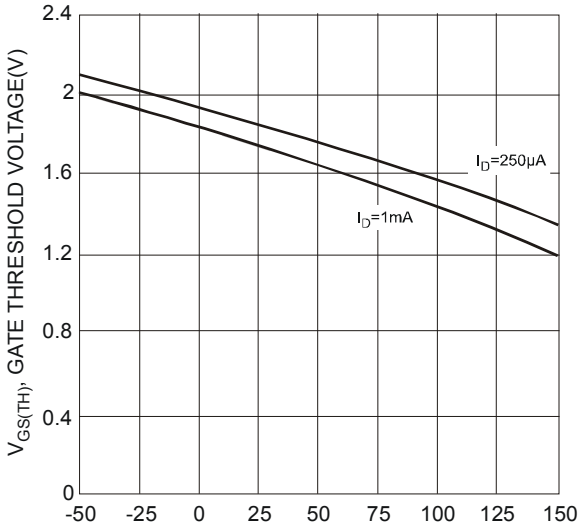


Fig. 7 Gate Threshold Variation vs. Ambient Temperature

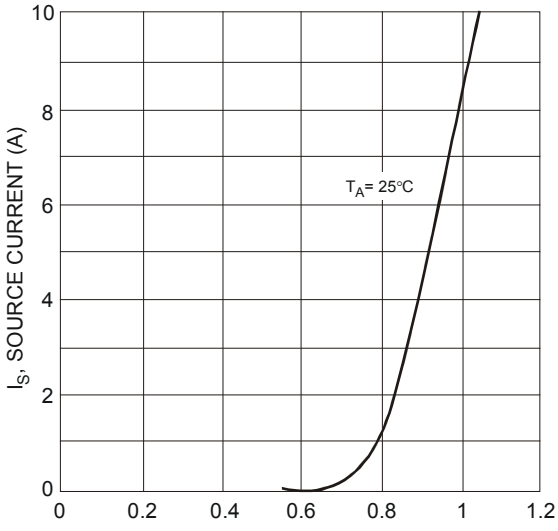


Fig. 8 Diode Forward Voltage vs. Current

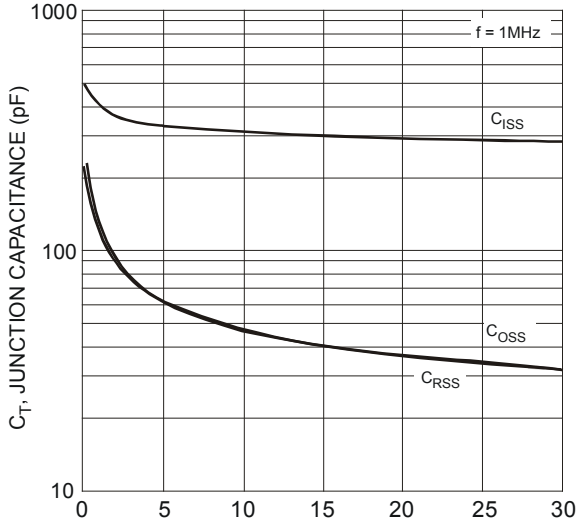


Fig. 9 Typical Junction Capacitance

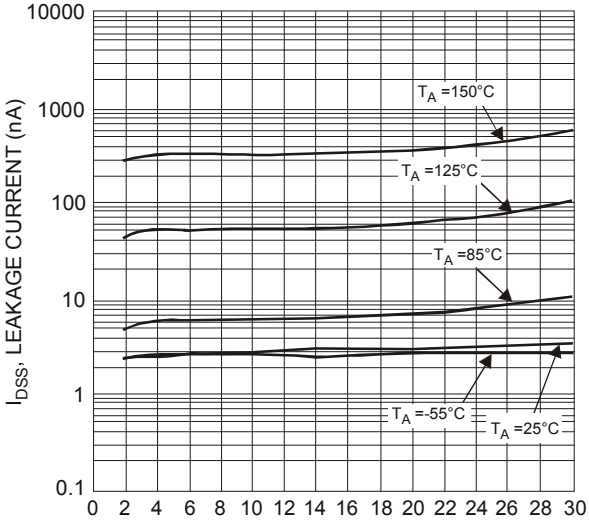


Fig. 10 Typical Drain-Source Leakage Current vs. Voltage

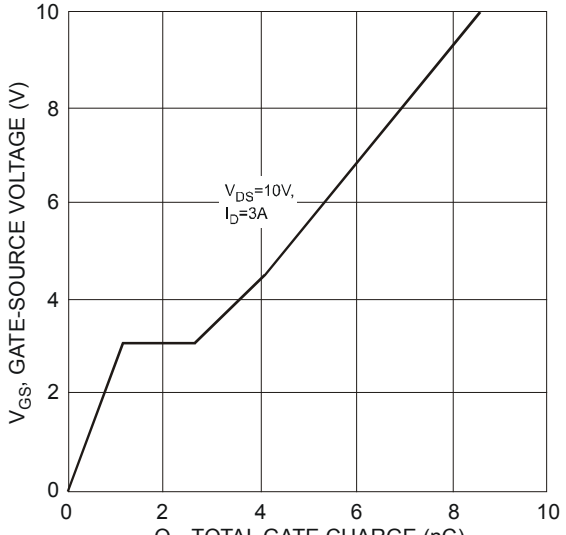


Fig. 11 Gate-Charge Characteristics

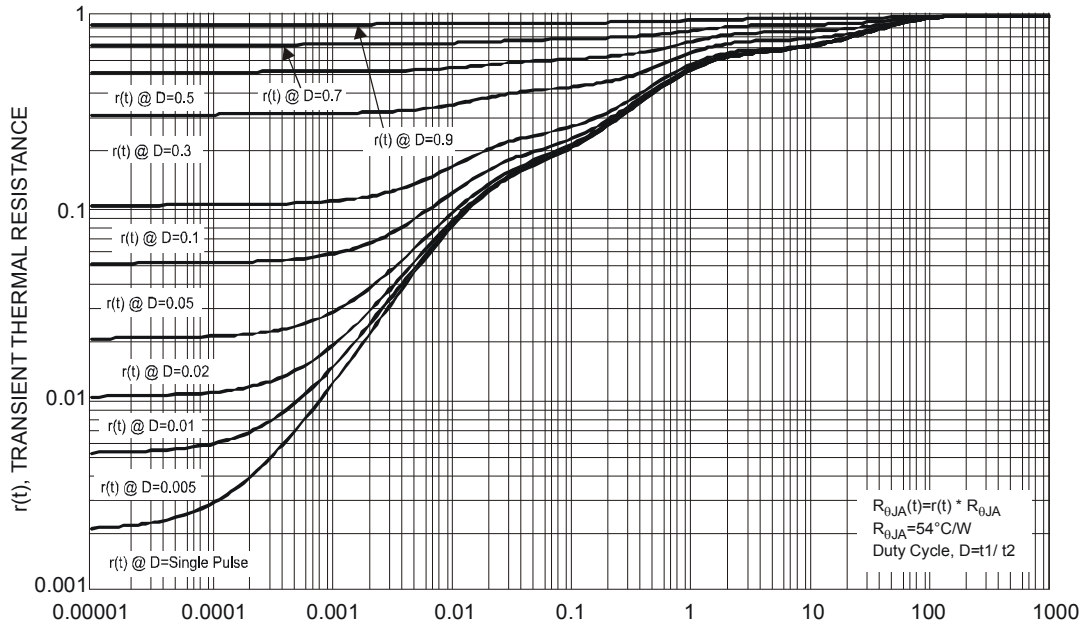
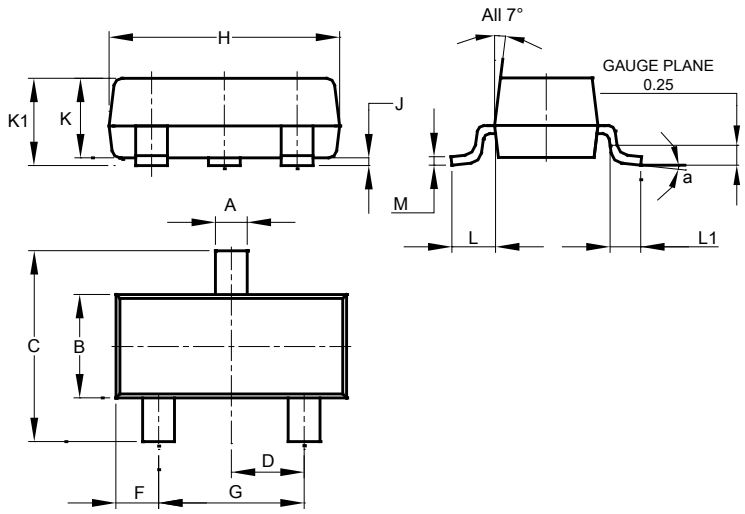


Fig. 12 Transient Thermal Resistance

Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT23

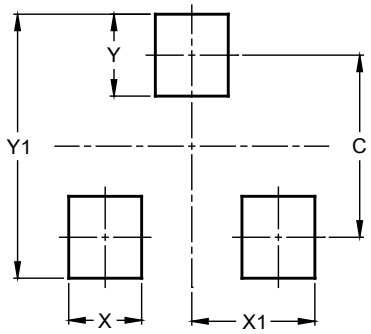


SOT23			
Dim	**Min**	**Max**	**Typ**
A	0.37	0.51	0.40
B	1.20	1.40	1.30
C	2.30	2.50	2.40
D	0.89	1.03	0.915
F	0.45	0.60	0.535
G	1.78	2.05	1.83
H	2.80	3.00	2.90
J	0.013	0.10	0.05
K	0.890	1.00	0.975
K1	0.903	1.10	1.025
L	0.45	0.61	0.55
L1	0.25	0.55	0.40
M	0.085	0.150	0.110
a	0°	8°	--
All Dimensions in mm			

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT23



Dimensions	Value (in mm)
C	2.0
X	0.8
X1	1.35
Y	0.9
Y1	2.9

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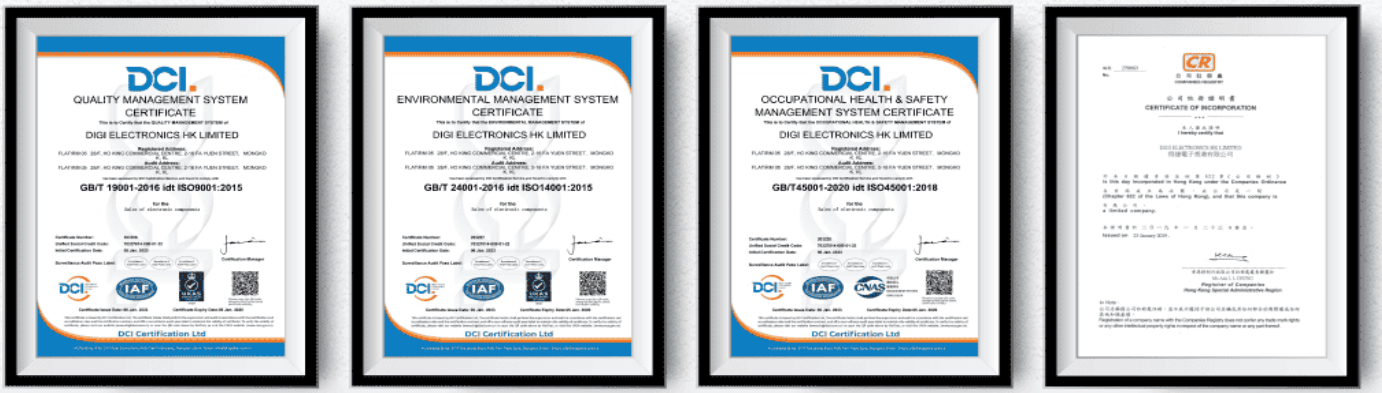

Tel: +00 852-30501935

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